



(43) International Publication Date
29 September 2005 (29.09.2005)

PCT

(10) International Publication Number
WO 2005/091361 A1

(51) International Patent Classification⁷: **H01L 23/29**,
21/56

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(21) International Application Number:

PCT/JP2005/004410

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PI, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date: 8 March 2005 (08.03.2005)

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SI, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-079597 19 March 2004 (19.03.2004) JP

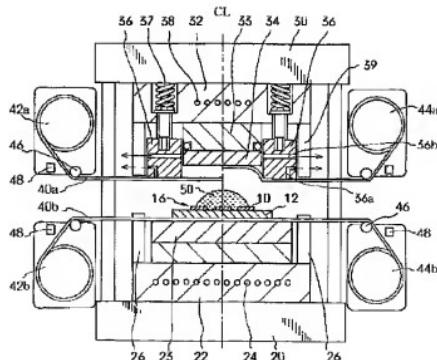
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(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THEREOF



(57) Abstract: A method of manufacturing a semiconductor device sealed in a cured silicone body by placing an unsealed semiconductor device into a mold and subjecting a liquid silicone composition that fills the spaces between the mold and the unsealed semiconductor device to compression molding under a predetermined molding temperature, wherein the curable liquid silicone composition has viscosity of 90 Pa·s or less at room temperature, a time interval from the moment directly after measurement of a torque with a curometer at the molding temperature to the moment when the torque reached 1 kgf·cm being not less than 1 min., while the time



Published:

— *with international search report*

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